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Modelling and Analytical Stability Analysis of Feedback Controlled Reactive Sputter Processes

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Introduction

• Why feedback controllers are used for reactive sputtering:



- Deposition Rate
- Stoichiometry
- Process stability –
 Short term
 Long term

3 fold increase in rate for SiO₂



How do we predict stability?

Approaches to evaluating stability

- Rule of thumb / best practice
- Simulation
- Analytic methods?



- Faster, more efficient
- Deeper insight
- Does not need interpretation can be automated!







- A model of reactive sputtering what kind of model?
- Low order required
- Berg model is ideal



Three states

Target compound coverage

Substrate compound coverage

Reactive gas partial pressure

 θ_t

 θ_s

р

$$\dot{p}(t) = \frac{k_B T_c}{V_c} \Big(q_{in}(t) - K_p p(t) - p(t) \overline{Fr} \alpha_t A_t \Big(1 - \theta_t(t) \Big) - p(t) \overline{Fr} \alpha_s A_s \Big(1 - \theta_s(t) \Big) \Big)$$

$$\dot{\theta_t}(t) = \frac{1}{\rho A_t} \Big(p(t) \overline{Fr} \alpha_t A_t a_t \Big(1 - \theta_t(t) \Big) - \frac{J}{e} Y_c A_t \theta_t(t) \Big)$$

$$\dot{\theta_s}(t) = \frac{1}{\rho A_s} \left(p(t) \overline{Fr} \alpha_s A_s a_s \left(1 - \theta_t(t) \right) + \frac{J}{e} Y_c A_t \theta_t(t) - \frac{J}{e} Y_m A_t \theta_s(t) \left(1 - \theta_t(t) \right) \right)$$

Dynamic behaviour of the reactive sputtering process, Kubart et al, thin solid films, 2006

MFC model







• Transport of gas from the MFC to the magnetron surface





- Target voltage feedback
- Filtering is present in the power supply and controller





$$u_c(t) = K2z(t) - K1w(t)$$
$$\dot{z}(t) = w_s - w$$







A single number that represents stability of the whole system!





Stability analysis method

A simple representation of stability





- Dual rotatable cathodes 4kW
- Al targets, O2 reactive gas
- Target voltage sensors
- Speedflo PDF controller







Closed loop with default controller parameters





Closed loop with default controller parameters





Closed loop with K1 increased to 3





Closed loop with K1 increased to 3





Software interface – automate analysis





Stability on a retro-fit reactive sputter tool



- AlOx reactive sputter deposition tool
- Planar cathodes 610mm x 130mm
- DC pulsed power, 5kW



Stability on a retro-fit reactive sputter tool

- Customer was unable to stabilise the process at the desired setpoint
- Automated and manual tuning was ineffective



80% compound coverage ratio



Stability on a retro-fit reactive sputter tool

- Model predicts unstable process control with default tuning parameters
- Is there a combination of tuning parameters that will stabilize the process?





• Cant solve this problem by tuning the controller





Stability on a retro-fit reactive sputter tool

Reduction in gas distribution pipe from 2m to 50cm





Stability on a retro-fit reactive sputter tool

- Gas pipe distribution modified so that MFC is on the chamber wall
- The process is now stabilizable at the required setpoint





Stability on a retro-fit reactive sputter tool

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Summary

- A simple tool for investigating and **predicting** the stability of a reactive sputter process
- Can be used at the system design stage or for troubleshooting problems
- Does not replace experimental (or automated) tuning of the controller

Future possibilities:

• Latest models

Journal of Physics D: Applied Physics

A time-dependent model for reactive sputter deposition K Strijckmans and D Depla Published 8 May 2014

- Co-sputtering, dual reactive gases
- Multiple process zones and gas injection points stability of interactions
- Software environment







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